

## Product Overview

### NGTB40N120FL2WA: IGBT, 1200 V Field Stop II, 40 A

For complete documentation, see the data sheet.

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop II Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss. In addition, this new device is packaged in a TO-247-4L package that provides significant reduction in Eon Losses compared to standard TO-247-3L package. The IGBT is well suited for UPS and solar applications. Incorporated into the device is a soft and fast co-packaged free wheeling diode with a low forward voltage.

#### Features

- TO-247-4L
- Extremely Efficient Trench with Field Stop Technology
- $T_{Jmax} = 175^{\circ}C$
- Improved Gate Control Lowers Switching Losses
- Separate Emitter Drive Pin
- Optimized for High Speed Switching
- These are Pb-Free Devices

#### Benefits

- Minimal Eon Losses

#### Applications

- Solar Inverter
- Uninterruptible Power Inverter Supplies (UPS)
- Neutral Point Clamp Topology

#### End Products

- Industrial

### Part Electrical Specifications

Product	Compliance	Status	$V_{ES}^{(BR)C}$ Typ (V)	$I_C$ Max (A)	$V_{GE(sat)}$ Typ (V)	$V_F$ Typ (V)	$E_{off}$ Typ (mJ)	$E_{on}$ Typ (mJ)	$T_{rr}$ Typ (ns)	$I_{rr}$ Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand ( $\mu s$ )	$E_{AS}$ Typ (mJ)	$P_D$ Max (W)	Co-Pack aged Diode	Package Type
NGTB40N120FL2WAG	Pb-free Halide free	Active	1200	40	2.1	2	1.1	1.7	270	16	313	-	-	536	Yes	TO-247-4

For more information please contact your local sales support at [www.onsemi.com](http://www.onsemi.com).

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